

DIGITRON SEMICONDUCTORS

2N1770A-2N1777A, 2N2619A

PHASE CONTROL SCR

Available Non-RoHS (standard) or RoHS compliant (add PBF suffix).

Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.

MAXIMUM RATINGS

Ratings	Symbol	2N1770A	2N1771A	2N1772A	2N1773A	2N1774A	Units
Repetitive peak off-state voltage	V_{DRM}	25	50	100	150	200	Volts
Repetitive peak reverse voltage	V_{RRM}	25	50	100	150	200	Volts
Non-repetitive peak reverse voltage	V_{RSM}	35	75	150	225	300	Volts

Ratings	Symbol	2N1775A	2N1776A	2N1777A	2N2619A	Units
Repetitive peak off-state voltage	V_{DRM}	250	300	400	600	Volts
Repetitive peak reverse voltage	V_{RRM}	250	300	400	600	Volts
Non-repetitive peak reverse voltage	V_{RSM}	350	400	500	720	Volts

Ratings	Symbol	2N1770A-2N1777A, 2N2619A	Units
RMS on-state current	$I_{T(RMS)}$	7.4	Amps
Average on-state current (nominal) $T_C = 105^\circ C$	$I_{T(AV)}$	4.7	Amps
Peak one-cycle surge (non-repetitive) on-state current (60 Hz)	I_{TSM}	60	Amps
I^2t (for fusing), 8.3ms	I^2t	15	A ² sec
Critical rate of rise of on-state current (repetitive)	di/dt	60	A/ μ s
Peak gate power dissipation	P_{GM}	5	Watts
Average gate power dissipation	$P_{G(AV)}$	0.5	Watts
Peak forward gate current	I_{FGM}	2	Amps
Peak reverse gate voltage	V_{RGM}	10	Volts
Storage temperature	T_{stg}	-65 to +150	$^\circ C$
Operating temperature	T_J	-65 to +150	$^\circ C$
Mounting torque	-	15	In.- lbs.
Mounting torque	-	17.5	kg-cm

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Test Conditions	2N1770A	2N1771A	2N1772A	2N1773A	2N1774A	Units
Voltage-Blocking state maximum Forward leakage, peak	I_{DRM}	$T_J = 150^\circ C, V_D = V_{DRM}$	9.0	9.0	9.0	8.0	6.0	mA
Reverse leakage, peak	I_{RRM}	$T_J = 150^\circ C, V_R = V_{RRM}$	9.0	9.0	9.0	8.0	6.0	mA

Characteristics	Symbol	Test Conditions	2N1775A	2N1776A	2N1777A	2N2619A	Units
Voltage-Blocking state maximum Forward leakage, peak	I_{DRM}	$T_J = 150^\circ C, V_D = V_{DRM}$	5.0	4.0	2.0	2.0	mA
Reverse leakage, peak	I_{RRM}	$T_J = 150^\circ C, V_R = V_{RRM}$	5.0	4.0	2.0	2.0	mA

Characteristics	Symbol	Test Conditions	2N1770A-2N1777A, 2N2619A			Units
			Min	Typ	Max	
Current- Conducting state Holding current	I_H	$V_D = 24V, R_L = 20\Omega, T_J = 25^\circ C$	-	-	25	mA
Peak on state voltage	V_{TM}	$T_C = 25^\circ C, I_{TM} = 15A$	-	-	1.85	Volts
Switching Typical critical dv/dt exponential to V_{DRM}	dv/dt	-	-	20	-	V/ μ s
Thermal Maximum thermal resistance, Junction to case	$R_{th(j-c)}$	-	-	-	3.1	$^\circ C/Watt$

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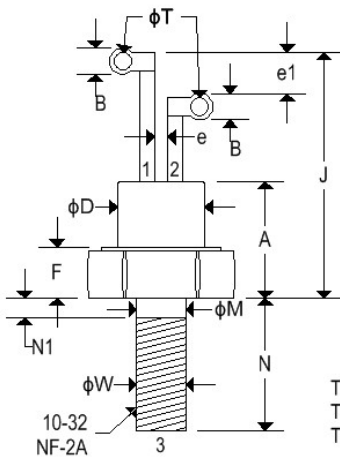
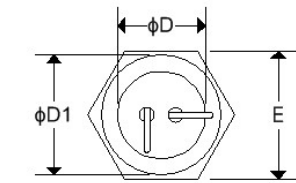
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Gate- Maximum parameters Gate current to trigger	I_{GT}	$V_D = 12V, R_L = 250\Omega, T_C = 25^\circ C$ $V_D = 12V, R_L = 250\Omega, T_C = -65^\circ C$	-	-	15 30	mA
	V_{GT}	$V_D = 12V, R_L = 250\Omega, T_C = 150^\circ C$	-	-	2.0	Volts
Gate voltage to trigger	V_{GD}	$V_D = 12V, R_L = 250\Omega, T_C = 150^\circ C$	-	-	2.0	Volts
Minimum non-triggering gate voltage	V_{GD}	$V_D = V_{DRM}, R_L = 250\Omega, T_C = 150^\circ C$	0.2	-	-	Volts

MECHANICAL CHARACTERISTICS

Case	TO-64
Marking	Alpha-numeric
Pin out	See below



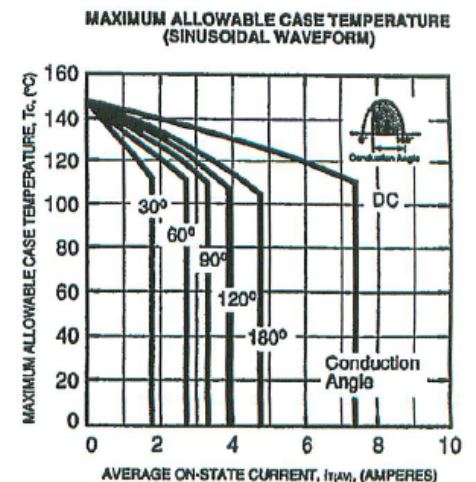
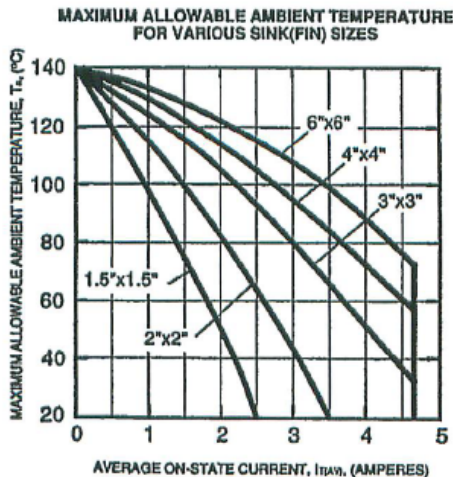
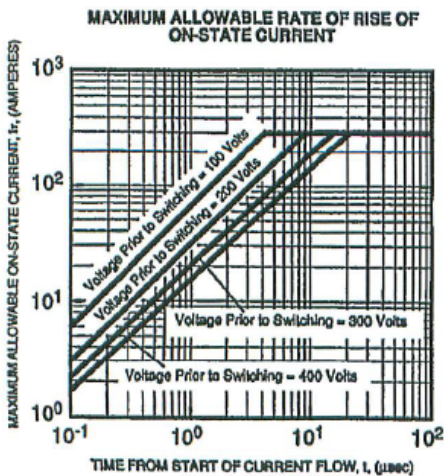
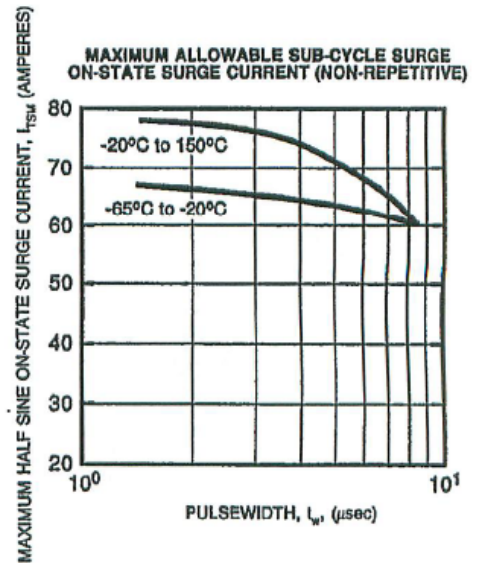
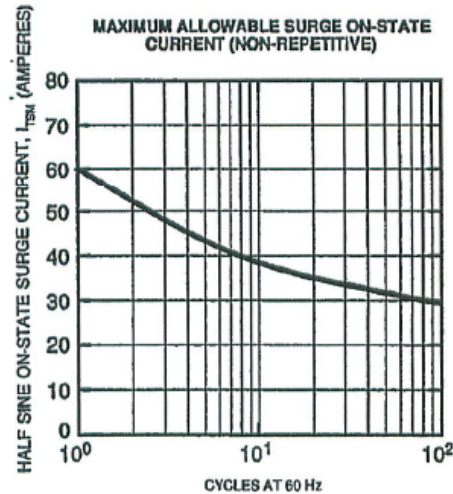
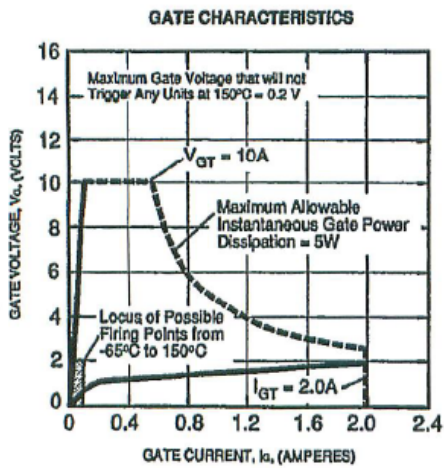
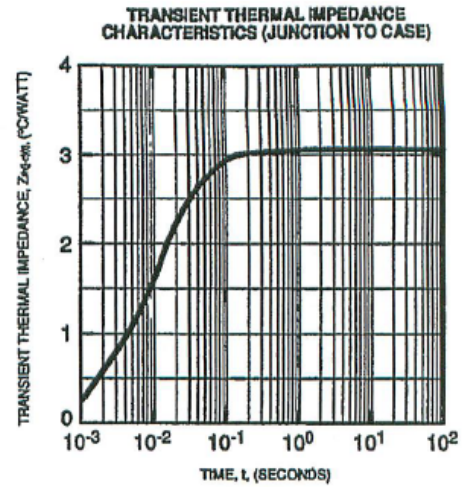
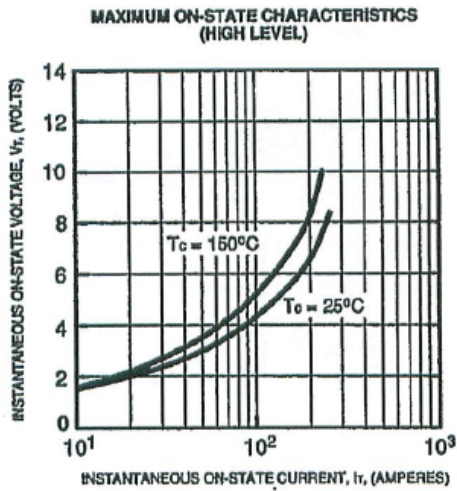
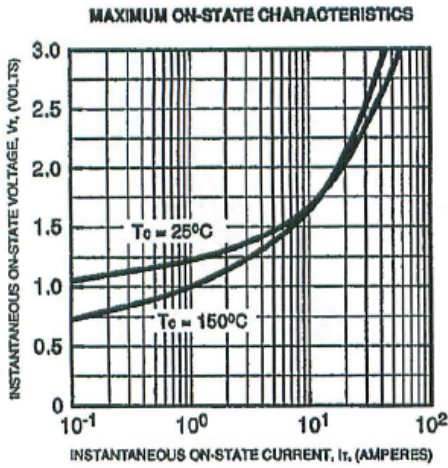
Terminal 1: Cathode
Terminal 2: Gate
Terminal 3: Anode (Stud)

	TO-64			
	Inches		Millimeters	
	Min	Max	Min	Max
A	0.300	0.400	7.620	10.160
B	0.080	0.136	2.030	3.450
ΦD	-	0.424	-	10.770
ΦD_1	0.400	-	10.160	-
E	0.424	0.437	10.770	11.100
e	0.013	-	0.330	-
e ₁	0.060	-	1.520	-
F	0.060	0.175	1.520	4.450
J	0.700	0.855	17.780	21.720
ΦM	0.163	0.189	4.140	4.800
N	0.400	0.453	10.160	11.510
N ₁	-	0.078	-	1.980
ΦT	0.040	0.075	1.020	1.910
ΦW	0.1658	0.1697	4.212	4.310

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